

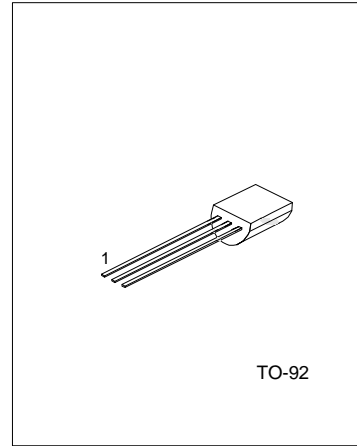
PLASTIC SILICON
CONTROLLED RECTIFIERS

DESCRIPTION

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-92 package which is readily adaptable for use in automatic insertion equipment.

DESCRIPTION

- *Sensitive Gate Trigger Current - 200µA Maximum
- *Low Reverse and forward Blocking Current - 100µA Maximum, Tc=125°C
- *Low Holding Current – 5mA Maximum
- *Glass-Passivated Surface for Reliability and Uniformity
- *Also Available with TO-5 or TO-18 Lead Form



1:CATHODE 2:GATE 3:ANODE

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX	UNIT
Thermal Resistance, Junction to Case	R _{θJC}	75	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	200	°C/W

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	MAX	UNIT
Peak Reverse Blocking Voltage	V _{RRM}		V
MCR100-4		200	
MCR100-6		400	
MCR100-8		600	
Forward Current RMS	I _{T(RMS)}	0.8	A
Peak Forward Surge Current, TA=25°C (1/2 cycle, Sine Wave, 60Hz)	I _{TSM}	10	A
Circuit Fusing Considerations, TA=25°C (t=1 to 8.3 ms)	I ² t	0.415	A ² s
Peak Gate Power – Forward, TA=25°C	P _{GM}	0.1	W
Average Gate Power – Forward, TA=25°C	P _{GF(AV)}	0.01	W
Peak Gate Current – Forward, TA=25°C(300µs, 120PPS)	I _{GF(M)}	1	A
Peak Gate Voltage - Reverse	V _{GRM}	5	V
Operating Junction Temperature Range @ Rated V _{RRM} and V _{DRM}	T _j	-65 to +110	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C
Lead Solder Temperature (<1/16" from case, 10 s max)		230	°C

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise stated)

PARAMETER	SYMBOL	MIN	MAX	UNIT
Peak Forward Blocking Voltage (T _c =125°C) MCR100-4 MCR100-6 MCR100-8	VDRM	200 400 600		V
Peak Forward or Reverse Blocking Current (Rated VDRM or VRRM) T _c =25°C T _c =125°C	IDRM, IRRM		10 100	μA μA
Forward "On" Voltage (Note1) (I _{TM} =1A peak @ T _A =25°C)	VTM		1.7	V
Gate Trigger Current (continuous dc) (Note 2) T _c =25 °C (Anode Voltage=7Vdc, R _L =100Ω)	IGT		200	μA
Gate Trigger Voltage (continuous dc) T _c =25 °C (Anode voltage=7Vdc, R _L =100Ω) T _c =40 °C (Anode Voltage=Rated VDRM, R _L =100Ω) T _c =125 °C	VGT		0.8 1.2	V
Holding Current T _c =25 °C (Anode Voltage=7Vdc, initiating current=20mA) T _c =40 °C	IH		5 10	mA

Notes: 1. Forward current applied for 1 ms maximum duration, duty cycle <=1%

2. RGK current is not included in measurement.